PEMB30; PUMB30

PNP/PNP double resistor-equipped transistors; R1 = 2.2 k Ω , R2 = open

Rev. 02 — 2 September 2009

Product data sheet

1. Product profile

1.1 General description

PNP/PNP double Resistor-Equipped Transistors (RET) in Surface-Mounted Device (SMD) plastic packages

Table 1. Product overview

Type number			NPN/PNP	NPN/NPN	
	NXP	JEITA	complement	complement	
PEMB30	SOT666	-	PEMD30	PEMH30	
PUMB30	SOT363	SC-88	PUMD30	PUMH30	

1.2 Features

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs

1.3 Applications

- Low current peripheral driver
- Control of IC inputs

Cost-saving alternative for BC857BS and BC857BV

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	tor					
V_{CEO}	collector-emitter voltage	open base	-	-	-50	V
I _O	output current		-	-	-100	mA
R1	bias resistor 1 (input)		1.54	2.2	2.86	kΩ



2. Pinning information

Table 3. Pinning

Pin	Description	Simplified outline	Symbol
1	•	Cimpiniou cumio	Cymioci
-	GND (emitter) TR1	6 5 4	6 5 4
2	input (base) TR1		
3	output (collector) TR2		R1
4	GND (emitter) TR2		TR2
5	input (base) TR2		TR1
6	output (collector) TR1	001aab555	R1 T
			1 2 3
			006aaa268

3. Ordering information

Table 4. Ordering information

Type number	Package		
	Name	Description	Version
PEMB30	-	plastic surface-mounted package; 6 leads	SOT666
PUMB30	SC-88	plastic surface-mounted package; 6 leads	SOT363

4. Marking

Table 5. Marking codes

Type number	Marking code ^[1]
PEMB30	2T
PUMB30	*B2

[1] * = -: made in Hong Kong

* = p: made in Hong Kong

* = t: made in Malaysia

* = W: made in China

5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor				
V_{CBO}	collector-base voltage	open emitter	-	-50	V
V_{CEO}	collector-emitter voltage	open base	-	-50	V
V_{EBO}	emitter-base voltage	open collector	-	-5	V
l _O	output current		-	-100	mA
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	-100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$			
tot	SOT363		<u>[1]</u> -	200	mW
	SOT666		[1][2]	200	mW
Per device)				
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C			
	SOT363		<u>[1]</u> _	300	mW
	SOT666		[1][2]	300	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor					
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air				
	SOT363		<u>[1]</u> -	-	625	K/W
	SOT666		[1][2] _	-	625	K/W
Per devic	e					
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air				
	SOT363		<u>[1]</u> _	-	416	K/W
	SOT666		[1][2]	-	416	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

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^[2] Reflow soldering is the only recommended soldering method.

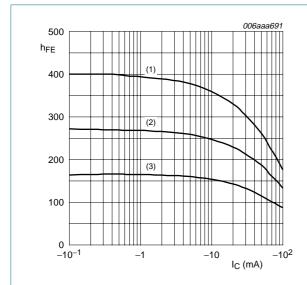
^[2] Reflow soldering is the only recommended soldering method.

7. Characteristics

Table 8. Characteristics

T_{amb} = 25 °C unless otherwise specified.

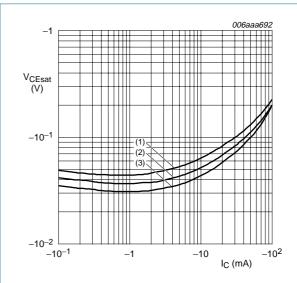
· anio – 20	e ameee emerwiee epec					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor					
I _{CBO}	collector-base cut-off current	$V_{CB} = -50 \text{ V}; I_E = 0 \text{ A}$	-	-	-100	nA
I _{CEO}	collector-emitter cut-off	$V_{CE} = -30 \text{ V}; I_{B} = 0 \text{ A}$	-	-	-1	μΑ
	current	$V_{CE} = -30 \text{ V}; I_{B} = 0 \text{ A};$ $T_{j} = 150 \text{ °C}$	-	-	-50	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0 \text{ A}$	-	-	-100	nA
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V}; I_C = -20 \text{ mA}$	30	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = -10 \text{ mA}; I_B = -0.5 \text{ mA}$	-	-	-150	mV
R1	bias resistor 1 (input)		1.54	2.2	2.86	kΩ
C _c	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	-	3	pF





- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -40 \, ^{\circ}C$

Fig 1. DC current gain as a function of collector current; typical values



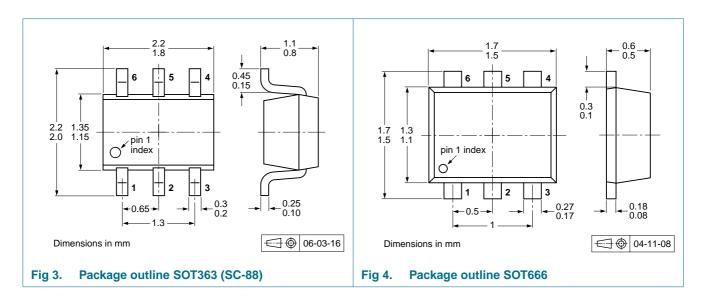
 $I_{\rm C}/I_{\rm B}=20$

- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -40 \, ^{\circ}C$

Fig 2. Collector-emitter saturation voltage as a function of collector current; typical values

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8. Package outline



9. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

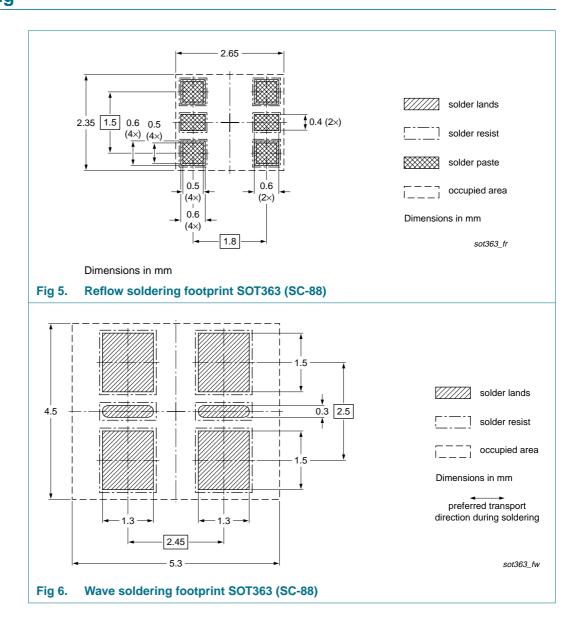
Type number	Package	Description	Packi	ng quar	ntity	
			3000	4000	8000	10000
PEMB30	SOT666	2 mm pitch, 8 mm tape and reel	-	-	-315	-
		4 mm pitch, 8 mm tape and reel	-	-115	-	-
PUMB30	SOT363	4 mm pitch, 8 mm tape and reel; T1	·115	-	-	-135
		4 mm pitch, 8 mm tape and reel; T2	-125	-	-	-165

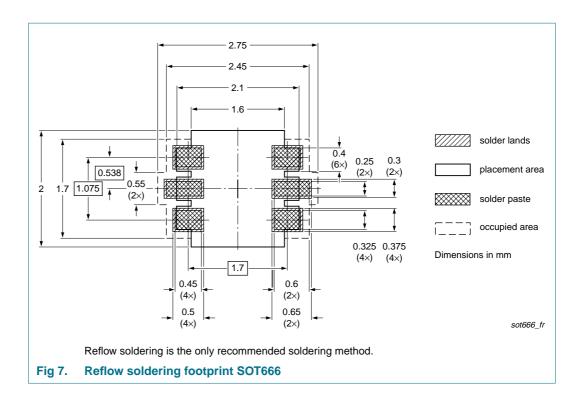
[1] For further information and the availability of packing methods, see <u>Section 13</u>.

[2] T1: normal taping

[3] T2: reverse taping

10. Soldering





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PNP/PNP double resistor-equipped transistors; R1 = 2.2 k Ω , R2 = open

11. Revision history

Table 10. Revision history

Release date	Data sheet status	Change notice	Supersedes		
20090902	Product data sheet	-	PEMB30_PUMB30_1		
	 This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content. 				
• Figure 3 "Package outline SOT363 (SC-88)": updated					
• Figure 5 "Re	flow soldering footprint SO	T363 (SC-88)": updated			
• Figure 6 "Wa	ave soldering footprint SOT	363 (SC-88)": updated			
• Figure 7 "Re	flow soldering footprint SO	T666": updated			
20060331	Product data sheet	-	-		
	 This data sh including ner content. Figure 3 "Pa Figure 5 "Re Figure 6 "Wa Figure 7 "Re 	 This data sheet was changed to reflect including new legal definitions and disciplination. Figure 3 "Package outline SOT363 (SC Figure 5 "Reflow soldering footprint SO") Figure 6 "Wave soldering footprint SOT Figure 7 "Reflow soldering footprint SOT 	 This data sheet was changed to reflect the new company name including new legal definitions and disclaimers. No changes we content. Figure 3 "Package outline SOT363 (SC-88)": updated Figure 5 "Reflow soldering footprint SOT363 (SC-88)": updated Figure 6 "Wave soldering footprint SOT363 (SC-88)": updated Figure 7 "Reflow soldering footprint SOT366": updated 		

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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